

CoolMOS™ Power Transistor
Features

- Lowest figure-of-merit $R_{ON} \times Q_g$
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant

CoolMOS CP is designed for:

- Hard switching SMPS topologies

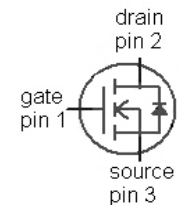
Product Summary

$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max} @ T_j = 25^\circ C$	0.6	Ω
$Q_{g,typ}$	21	nC

PG-TO262



Type	Package	Marking
IPI60R600CP	PG-TO262	6R600P


Maximum ratings, at $T_j = 25^\circ C$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C = 25^\circ C$	6.1	A
		$T_C = 100^\circ C$	3.8	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C = 25^\circ C$	15	
Avalanche energy, single pulse	E_{AS}	$I_D = 2.2 A, V_{DD} = 50 V$	144	mJ
Avalanche energy, repetitive t_{AR} ^{2),3)}	E_{AR}	$I_D = 2.2 A, V_{DD} = 50 V$	0.2	
Avalanche current, repetitive t_{AR} ^{2),3)}	I_{AR}		2.2	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} = 0 \dots 480 V$	50	V/ns
Gate source voltage	V_{GS}	static	± 20	V
		AC ($f > 1 Hz$)	± 30	
Power dissipation	P_{tot}	$T_C = 25^\circ C$	60	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	$^\circ C$

Maximum ratings, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	$T_C=25\text{ }^\circ\text{C}$	3.3	A
Diode pulse current ²⁾	$I_{S,pulse}$		15	
Reverse diode dv/dt ⁴⁾	dv/dt		15	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	2.1	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	62	
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	1.6 mm (0.063 in.) from case for 10 s	-	-	260	$^\circ\text{C}$

Electrical characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified
Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=220\text{ }\mu\text{A}$	2.5	3	3.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$	-	-	1	μA
		$V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ }^\circ\text{C}$	-	10	-	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=3.3\text{ A}, T_j=25\text{ }^\circ\text{C}$	-	0.54	0.6	Ω
		$V_{GS}=10\text{ V}, I_D=3.3\text{ A}, T_j=150\text{ }^\circ\text{C}$	-	1.5	-	
Gate resistance	R_G	$f=1\text{ MHz}, \text{open drain}$	-	1.5	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	550	-	pF
Output capacitance	C_{oss}		-	28	-	
Effective output capacitance, energy related ⁵⁾	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V	-	26	-	
Effective output capacitance, time related ⁶⁾	$C_{o(tr)}$		-	67	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=3.3\text{ A},$ $R_G=23.1\ \Omega$	-	17	-	ns
Rise time	t_r		-	12	-	
Turn-off delay time	$t_{d(off)}$		-	75	-	
Fall time	t_f		-	17	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD}=480\text{ V}, I_D=3.3\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	2	-	nC
Gate to drain charge	Q_{gd}		-	10	-	
Gate charge total	Q_g		-	21	27	
Gate plateau voltage	$V_{plateau}$		-	4.7	-	V

Reverse Diode

Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=3.3\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.8	1.2	V
Reverse recovery time	t_{rr}	$V_R=400\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	220	-	ns
Reverse recovery charge	Q_{rr}		-	2.3	-	μC
Peak reverse recovery current	I_{rrm}		-	18	-	A

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

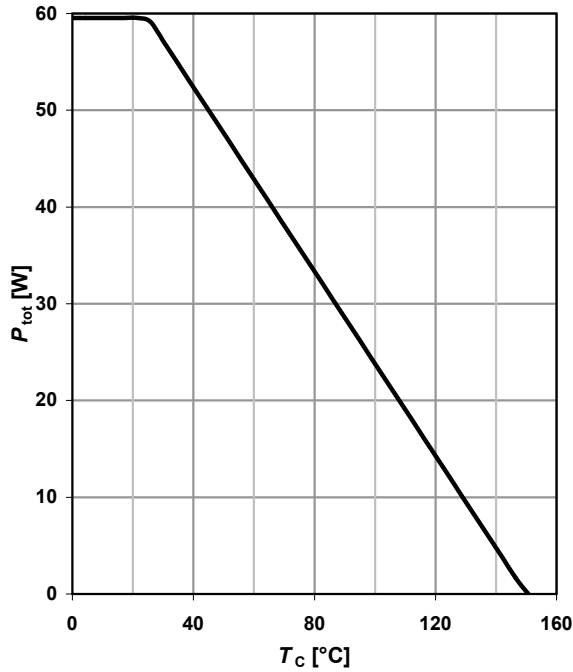
⁴⁾ $I_{SD}=I_D, di/dt \leq 400\text{ A}/\mu\text{s}, V_{DClink}=400\text{ V}, V_{peak} < V_{(BR)DSS}, T_j < T_{j,max}$, identical low side and high side switch

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁶⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

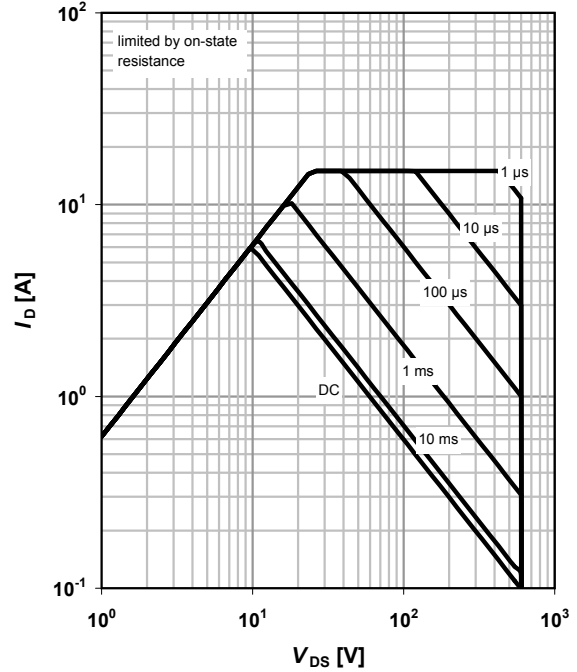
$P_{tot}=f(T_C)$



2 Safe operating area

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

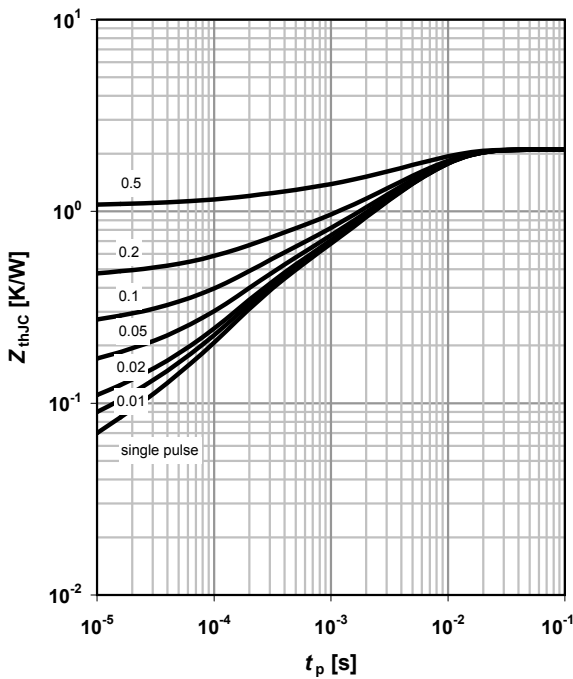
parameter: t_p



3 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

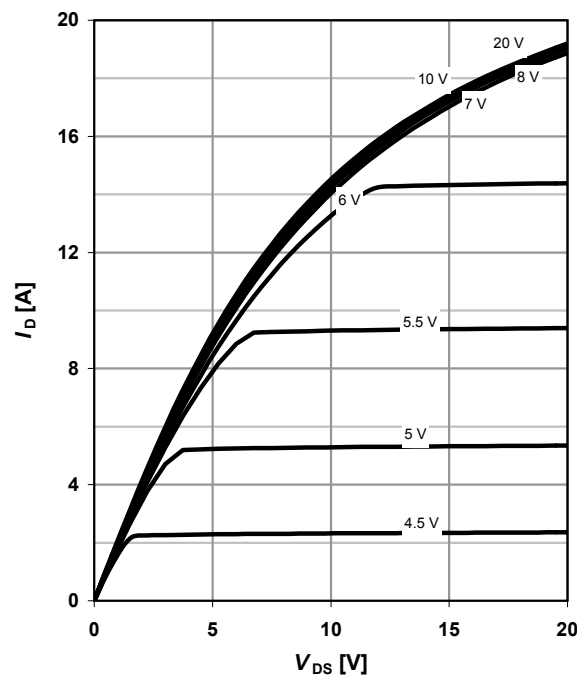
parameter: $D=t_p/T$



4 Typ. output characteristics

$I_D=f(V_{DS}); T_j=25\text{ °C}$

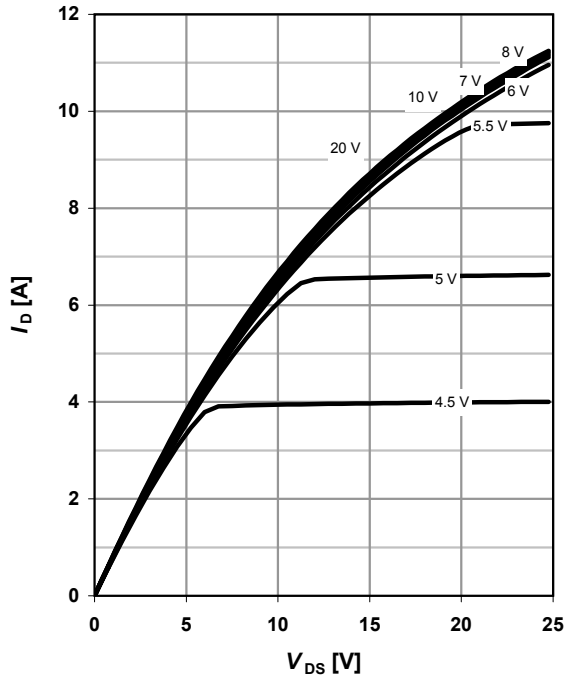
parameter: V_{GS}



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 150\text{ }^\circ\text{C}$

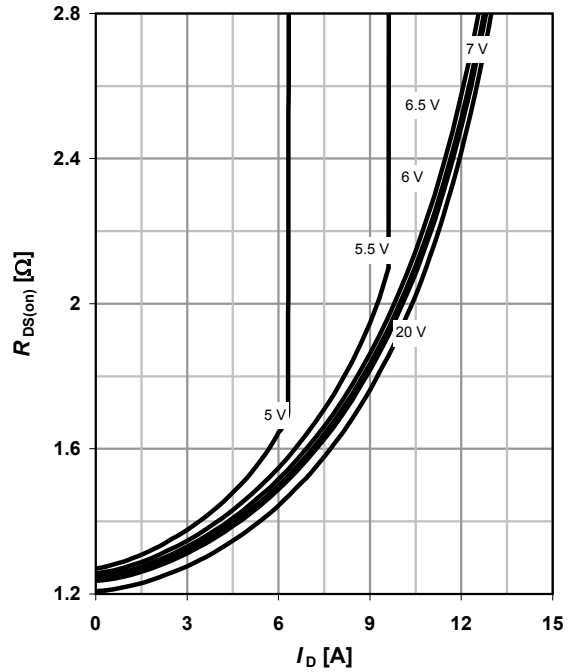
parameter: V_{GS}



6 Typ. drain-source on-state resistance

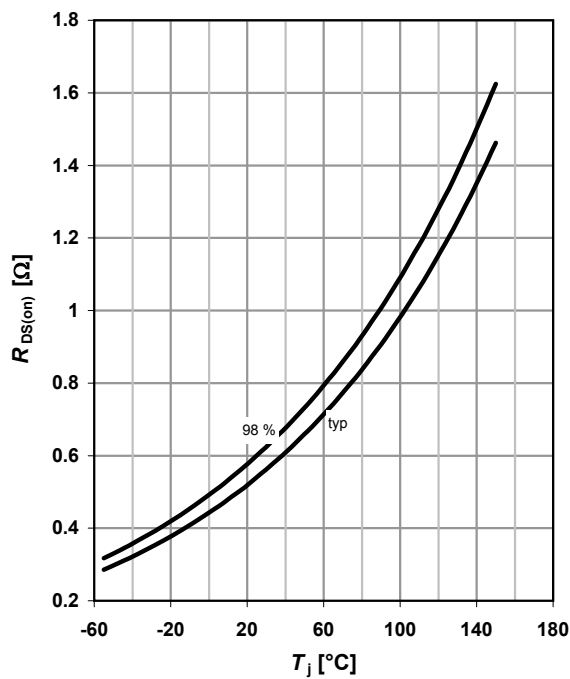
$R_{DS(on)} = f(I_D); T_j = 150\text{ }^\circ\text{C}$

parameter: V_{GS}



7 Drain-source on-state resistance

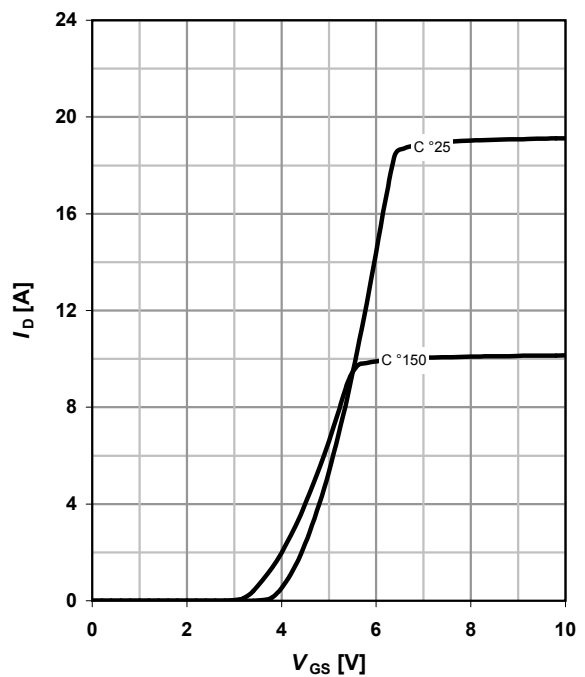
$R_{DS(on)} = f(T_j); I_D = 3.3\text{ A}; V_{GS} = 10\text{ V}$



8 Typ. transfer characteristics

$I_D = f(V_{GS}); |V_{DS}| > 2I_D/R_{DS(on)max}$

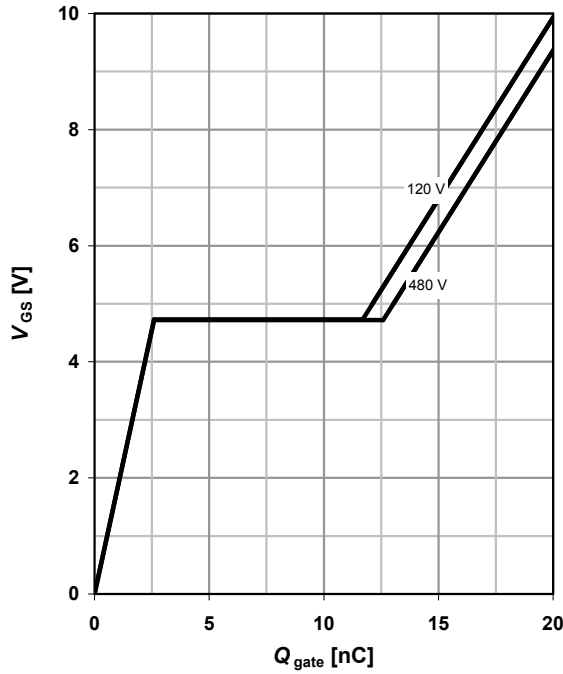
parameter: T_j



9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=3.3\text{ A pulsed}$

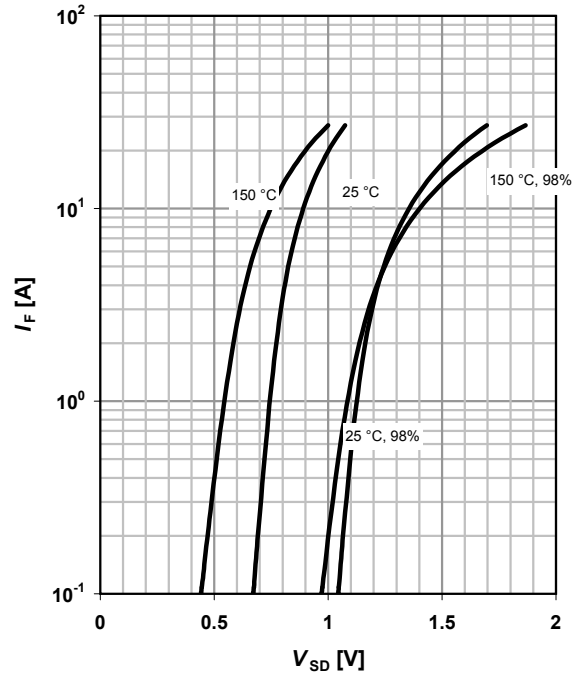
parameter: V_{DD}



10 Forward characteristics of reverse diode

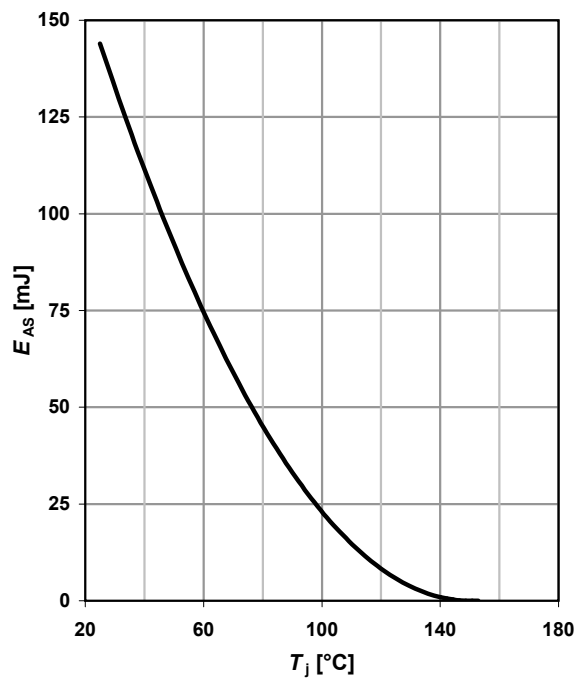
$I_F=f(V_{SD})$

parameter: T_j



11 Avalanche energy

$E_{AS}=f(T_j); I_D=2.2\text{ A}; V_{DD}=50\text{ V}$



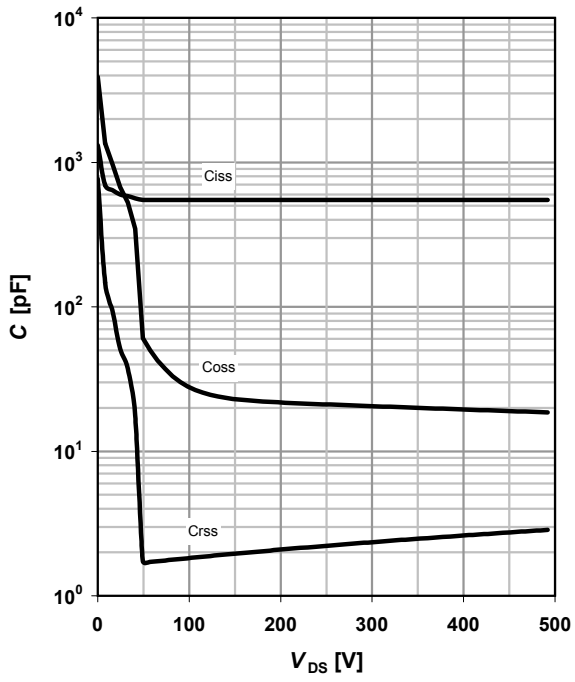
12 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$



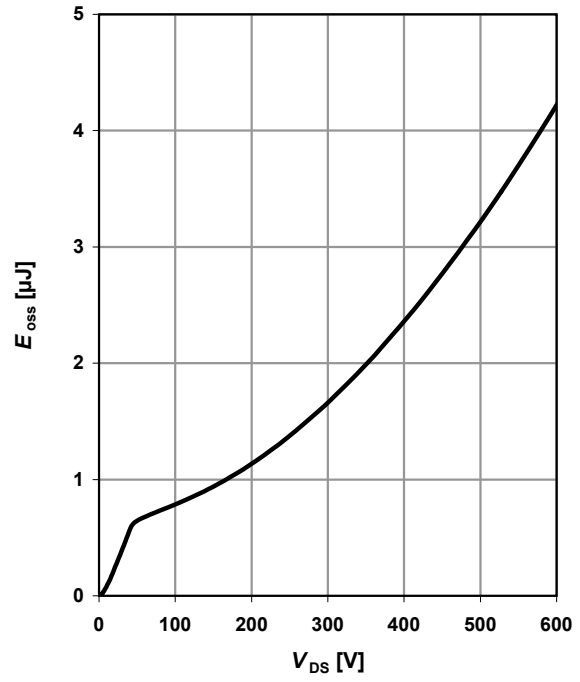
13 Typ. capacitances

$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



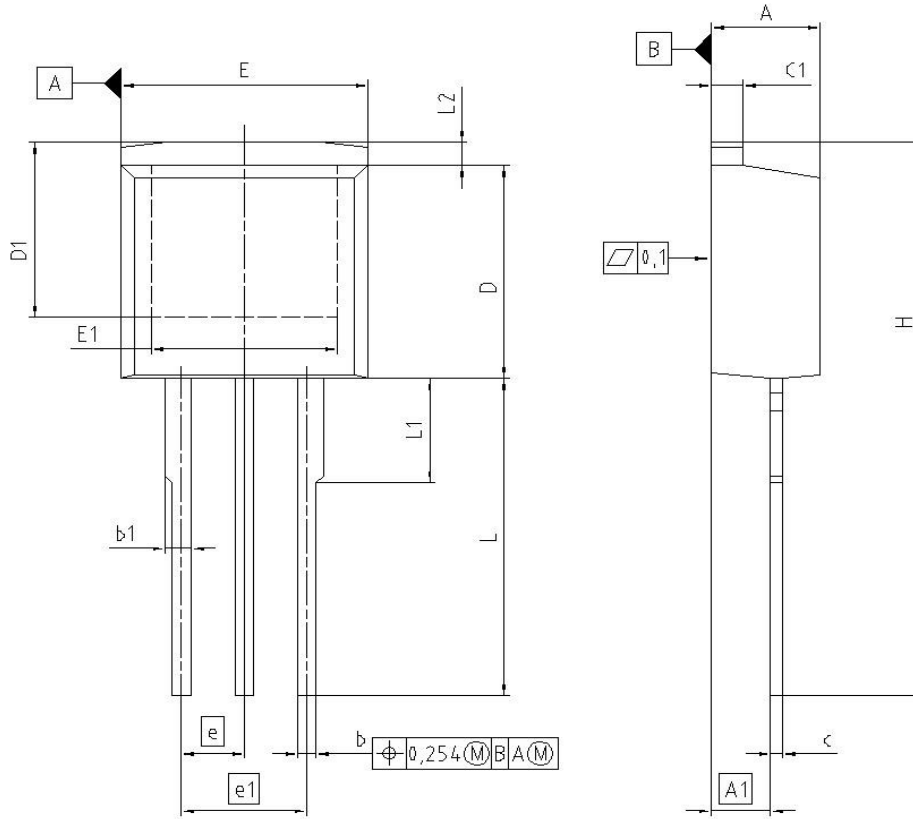
14 Typ. Coss stored energy

$E_{oss} = f(V_{DS})$



Definition of diode switching characteristics





DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.500	0.169	0.177
A1	2.150	2.650	0.085	0.104
b	0.650	0.850	0.026	0.033
b1	0.635	1.400	0.025	0.055
c	0.400	0.600	0.016	0.024
c1	1.170	1.370	0.046	0.054
D	9.050	9.450	0.356	0.372
D1	6.900	7.650	0.272	0.301
E	9.800	10.200	0.386	0.402
E1	7.250	8.600	0.285	0.339
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
L	13.000	14.000	0.512	0.551
L1	4.350	4.750	0.171	0.187
L2	0.700	1.300	0.028	0.051

REFERENCE
JEDEC TO262

SCALE

EUROPEAN PROJECTION

ISSUE DATE
01-06-2005

FILE
TO262_1

Dimensions in mm/inches

Published by
Infineon Technologies AG
81726 Munich, Germany
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